



WBFBP-03D Plastic-Encapsulate Diodes

DKN222LLD03 SWITCHING DIODE

DESCRIPTION

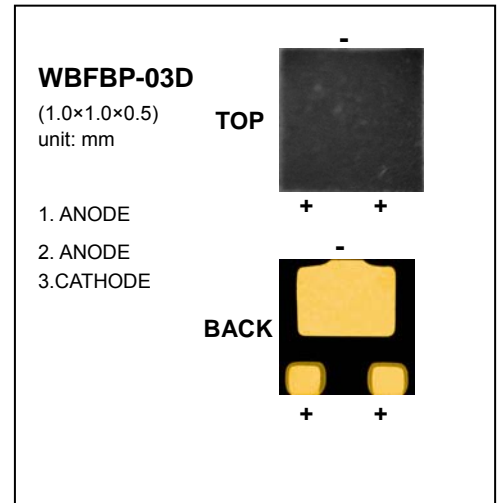
Epitaxial Planar Silicon Diode

FEATURES

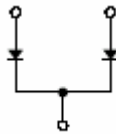
High speed
Suitable for high packing density layout
High reliability

APPLICATION

Ultra high speed switching
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



MARKING:



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25 °C

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V_{RM}	80	V
DC reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	300	mA
Average forward current	I_O	100	mA
Power dissipation	P_D	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=70V$		0.1	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_D	$V_R=6V, f=1MHz$		3.5	pF
Reverse recovery time	t_{rr}	$V_R=6V, I_F=5mA$		4	ns